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Ultrafast recovery diode

Main product characteristics

I _{F(AV)}	15 A
V _{RRM}	200 V
T _j (max)	175° C
V _F (typ)	0.85 V
t _{rr} (typ)	20 ns

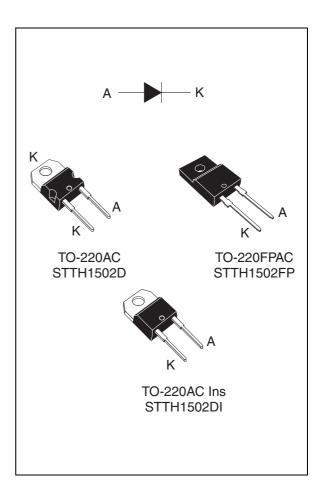
Features and benefits

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery time
- High junction temperature
- Insulated packages
 - TO-220FPAC Electrical insulation 2000 V_{DC}
 - TO-220AC Ins Electrical insulation 2500 V_{RMS}

Description

The STTH1502 uses ST's new 200V planar Pt doping technology, and is specially suited for switching mode base drive and transistor circuits.

Packaged in TO-220AC, TO-220FPAC, and TO-220 Ins, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection.



Order codes

Part Number	Marking
STTH1502D	STTH1502
STTH1502FP	STTH1502
STTH1502DI	STTH1502DI



1 Characteristics

Table 1. Absolute ratings (limiting values at $T_j = 25^{\circ}$ C, unless otherwise specified)

Symbol	Para	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage	200	V		
I _{F(RMS)}	RMS forward current			32	А
		TO-220AC	T _c = 130° C		
I _{F(AV)}	Average forward current, $\delta = 0.5$ TO-220AC Ins	TO-220AC Ins	T _c = 105° C	15	А
	TO-220FPAC $T_c = 85^{\circ} C$				
I _{FSM}	Surge non repetitive forward current t _p = 10 ms Sinusoidal				А
T _{stg}	Storage temperature range				°C
Тj	Maximum operating junction temperature				°C

Table 2.Thermal parameters

Symbol	Parameter	Value	Unit	
		TO-220AC	2.5	
R _{th(j-c)}	Junction to case	TO-220AC Ins	3.8	° C/W
		TO-220FPAC	5	

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _R ⁽¹⁾	Poverse leakage ourrent	$T_j = 25^\circ C$	V - V			10	
I _R ⁽¹⁾ Reverse leakage current	T _j = 125° C	V _R = V _{RRM}		10	100	μA	
		$T_j = 25^\circ C$	l _F = 15 A		1	1.1	
		T _j = 150° C	IF = 13 A		0.85	0.95	
V _F ⁽²⁾	Forward voltage drop	T _j = 125° C	I _F = 30 A		1.05	1.20	V
		T _j = 25° C	I _F = 30 A		1.15	1.3	
		T _j = 150° C	1F = 30 A		1	1.15	

1. Pulse test: $t_p = 5 \text{ ms}, \delta < 2 \%$

2. Pulse test: t_p = 380 μ s, δ < 2 %

To evaluate the conduction losses use the following equation: P = 0.74 x $I_{F(AV)}$ + 0.014 ${I_F}^2_{(RMS)}$



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Table 4.	Dynamic characteristics
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		-				
Symbol	Parameter	Test conditions	Min.	Тур	Max.	Unit
÷	Reverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A}/\mu\text{s},$ $V_R = 30 \text{ V, } T_j = 25^\circ \text{ C}$		28	36	ns
t _{rr}	neverse recovery time	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = -100 \text{ A}/\mu\text{s},$ $V_R = 30 \text{ V}, \text{ T}_j = 25^\circ \text{ C}$		20	25	
I _{RM}	Reverse recovery current	$I_F = 15 \text{ A}, \text{ d}I_F/\text{d}t = -200 \text{ A}/\mu\text{s},$ $V_R = 160 \text{ V}, \text{ T}_j = 125^\circ \text{ C}$		5.7	7.2	А
t _{fr}	Forward recovery time	I_F = 15 A, dI _F /dt = 50 A/µs V _{FR} = 1.1 x V _{Fmax} , T _j = 25° C		200		ns
V _{FP}	Forward recovery voltage	$I_F = 15 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s},$ $T_j = 25^{\circ} \text{ C}$		1.3		V



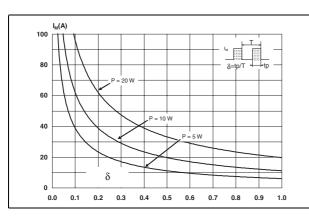
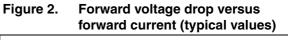


Figure 3. Forward voltage drop versus forward current (maximum values)



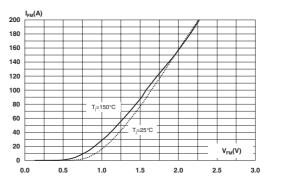


Figure 4. Relative variation of thermal impedance, junction to case, versus pulse duration (TO-220AC)

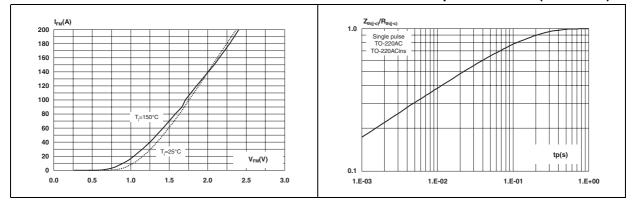
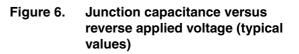


Figure 5. **Relative variation of thermal** impedance, junction to case, versus pulse duration (TO-220FPAC)



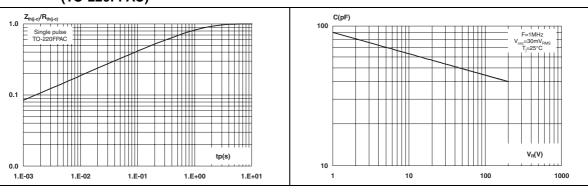
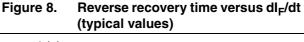


Figure 7. **Reverse recovery charges versus** dl_F/dt (typical values)



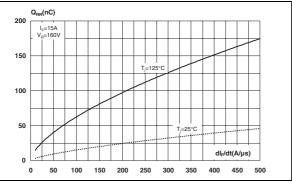


Figure 9. Peak reverse recovery current versus dl_F/dt (typical values)

t_{RR}(ns) 80

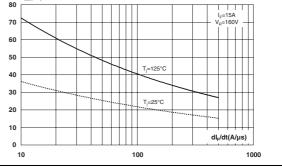
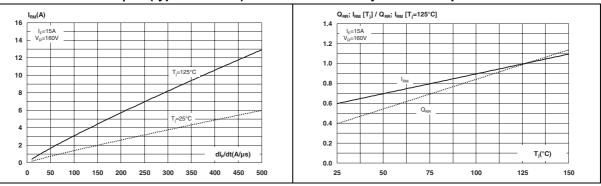


Figure 10. Dynamic parameters versus junction temperature



2 Ordering information scheme

Ultrafast switching diode	
Average forward current	
15 = 15 A	
Repetitive peak reverse voltage	je
02 = 200 V	
Package	
D = TO-220AC FP = TO-220FPAC DI = TO-220AC Ins	



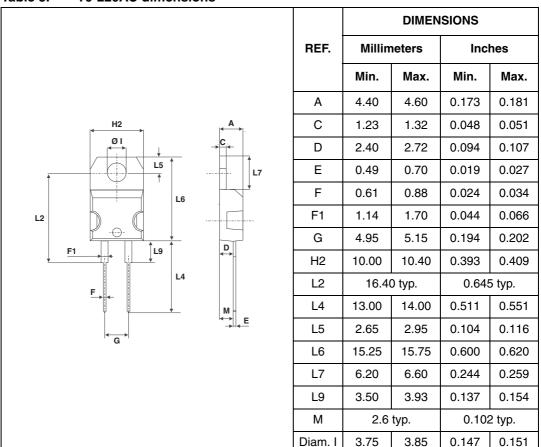
3 Package information

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.8 Nm

Maximum torque value: 1.0 Nm







			DIMEN	SIONS	
	REF	Millim	eters	hes	
		Min.	Max.	Min.	Max.
	Α	4.4	4.6	0.173	0.181
	В	2.5	2.7	0.098	0.106
	D	2.5	2.75	0.098	0.108
Dia	Е	0.45	0.70	0.018	0.027
	F	0.75	1	0.030	0.039
	F1	1.15	1.70	0.045	0.067
	G	4.95	5.20	0.195	0.205
	G1	2.4	2.7	0.094	0.106
	Н	10	10.4	0.393	0.409
L4	L2	16	Гур.	0.63	Тур.
	L3	28.6	30.6	1.126	1.205
	L4	9.8	10.6	0.386	0.417
' <mark>← G</mark> →'	L5	2.9	3.6	0.114	0.142
	L6	15.9	16.4	0.626	0.646
	L7	9.00	9.30	0.354	0.366
	Dia.	3.00	3.20	0.118	0.126

Table 6.T0-220FPAC dimensions



				Dimer	nsions		
	Ref.	M	illimete	ers		Inches	
		Min.	Тур.	Max.	Min.	Тур.	Max.
	А	15.20		15.90	0.598		0.625
в С	a1		3.75			0.147	
	a2	13.00		14.00	0.511		0.551
	В	10.00		10.40	0.393		0.409
	b1	0.61		0.88	0.024		0.034
14 A	b2	1.23		1.32	0.048		0.051
	С	4.40		4.60	0.173		0.181
	c1	0.49		0.70	0.019		0.027
12 a2	c2	2.40		2.72	0.094		0.107
	е	4.80		5.40	0.189		0.212
	F	6.20		6.60	0.244		0.259
≪ 	ØI	3.75		3.85	0.147		0.151
	14	15.80	16.40	16.80	0.622	0.646	0.661
	L	2.65		2.95	0.104		0.116
	12	1.14		1.70	0.044		0.066
	М		2.60			0.102	

Table 7. TO-220AC Ins. dimensions

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.



4 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH1502D	STTH1502	TO-220AC	1.86 g	50	Tube
STTH1502FP	STTH1502	TO-220FPAC	2.2 g	50	Tube
STTH1502DI	STTH1502DI	TO-220AC Ins	1.86	50	Tube

5 Revision history

Date	Revision	Description of Changes
05-Apr-2006	1	First issue
10-Oct-2006	2	Added TO-220AC Ins package



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